ELIONIX

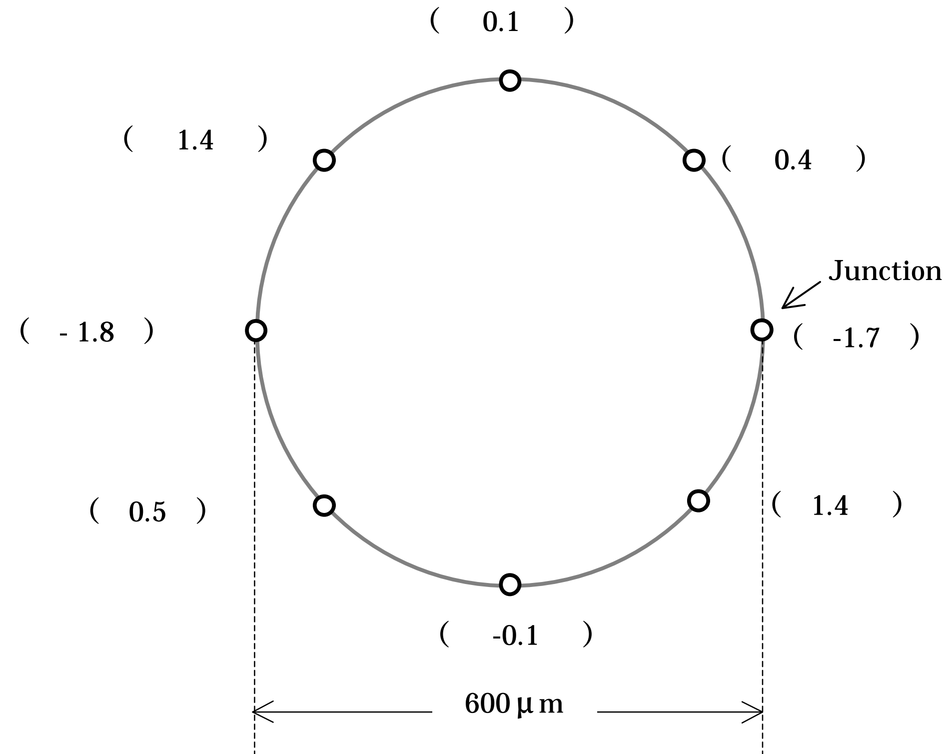
Circle pattern

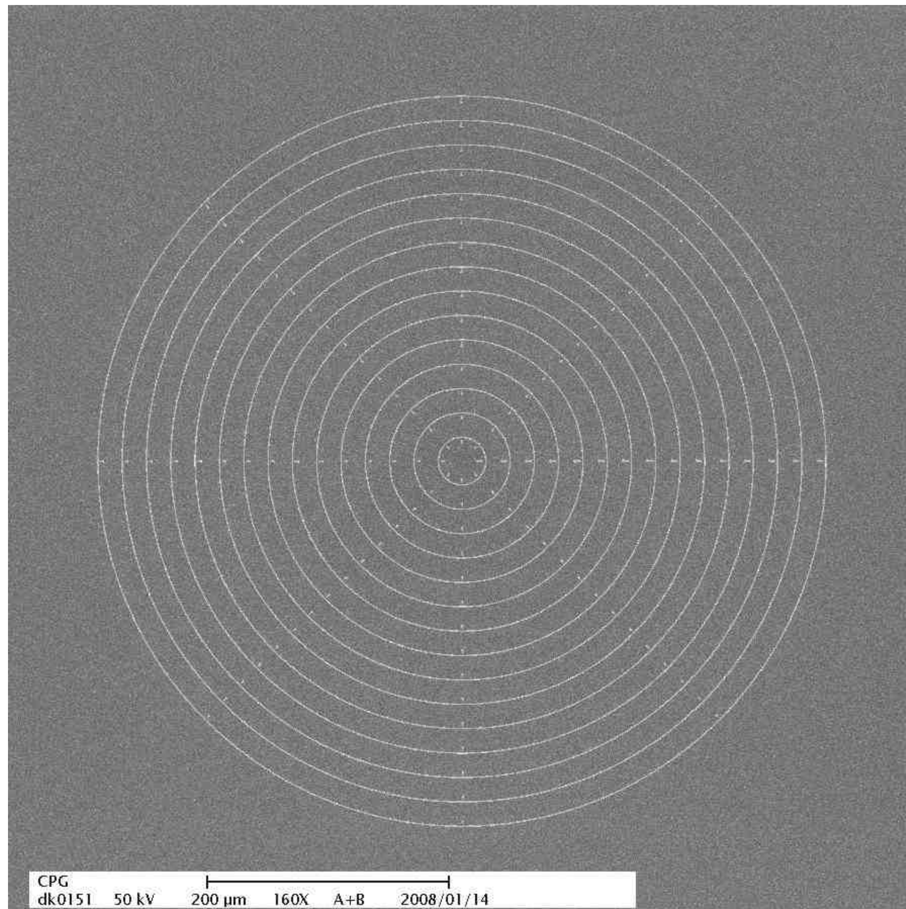
ACCEL. VOLT.	50 kV	EXT.VOLTAGE	3.9 kV
Emission CURR.	68 uA	CATHODE HEAT.	2.31 A
BEAM CURR.	100 pA	OL APERTURE	0.30 mmφ
FIELD SIZE	0.6 mm□	Dot Map	60000 dot
DOSE TIME	4.50 usec/dot	RESIST NAME	ZEP-520A
SUBSTRATE	Si-wafer	RESIST THIKNESS	0.30 um
Development temp	room temp ℃	Development time	360 sec

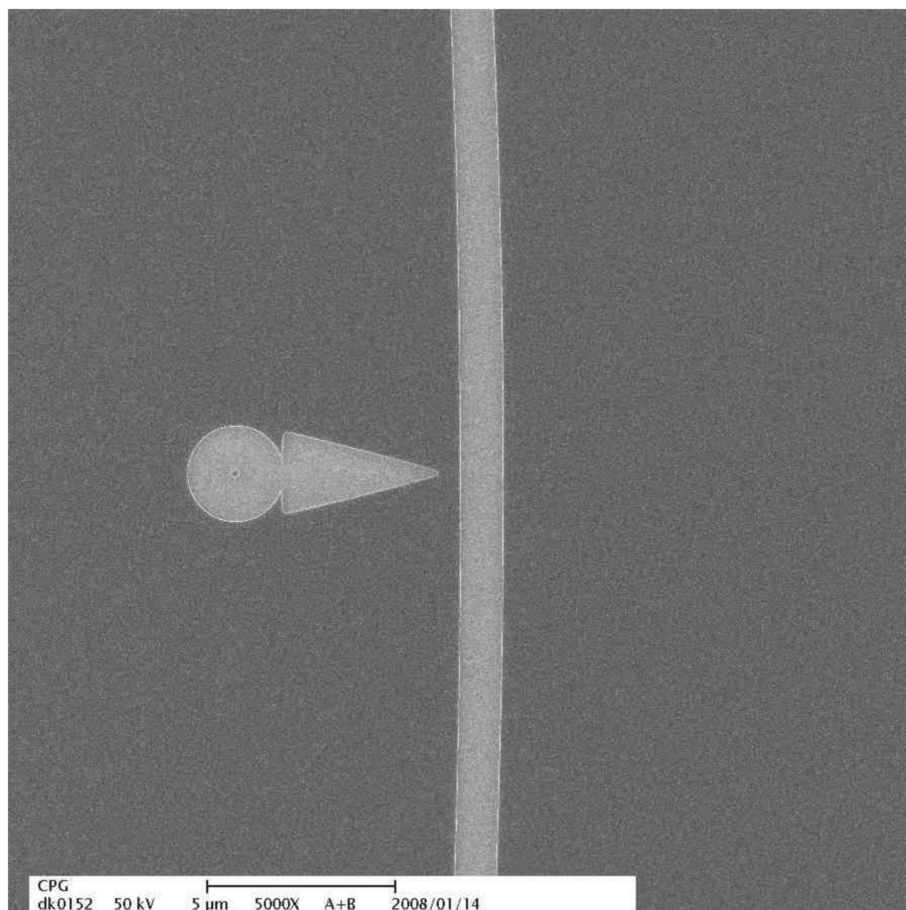
Measured ：

	Standard	Measured
Fitting circle	600 um±2%	595.7um
Max. deviation	≦±5um	1.4 um

The value in ( ) are the deviation between the points on the circle pattern and the circle fitted by least squares method.
［unit：μm］



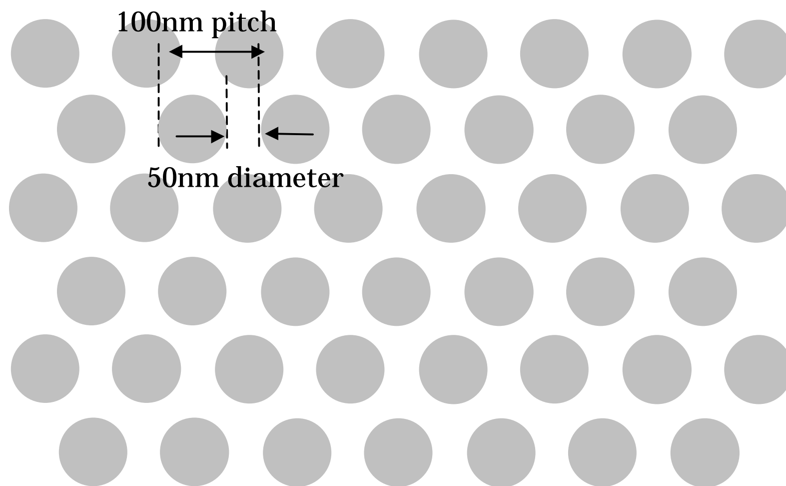

CPG
dk0151 50 kV 200 µm 160X A+B 2008/01/14

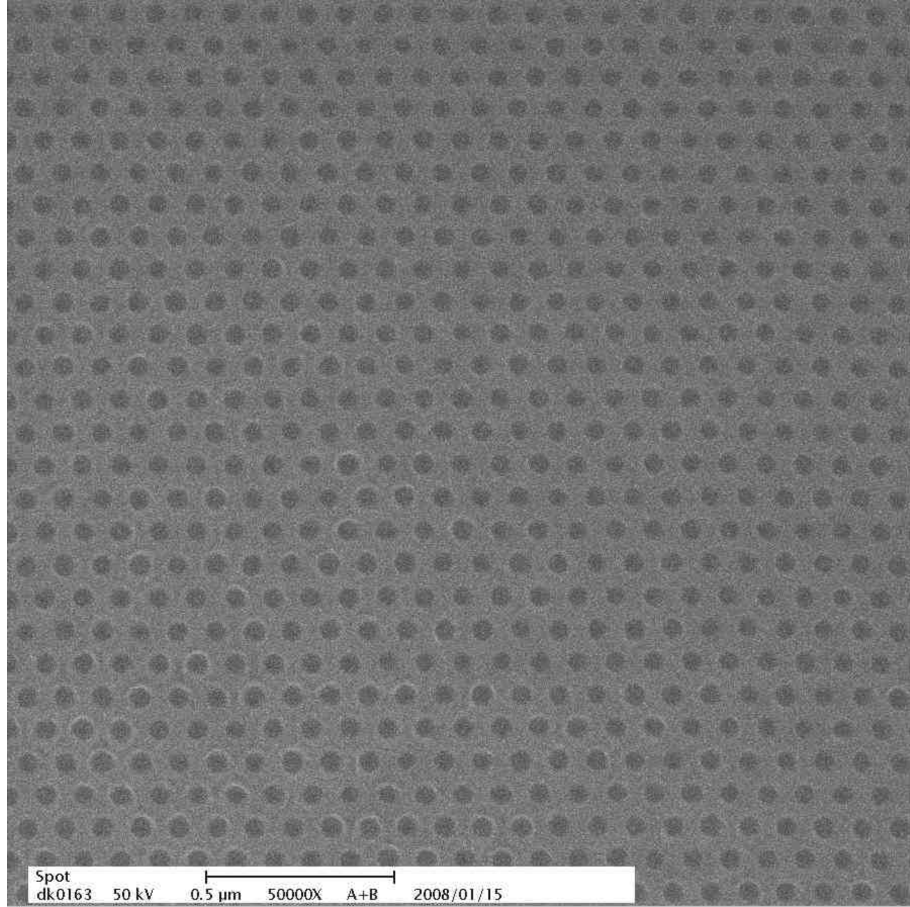

CPG
dk0152 50 kV 5 µm 5000X A+B 2008/01/14

ELIONIX

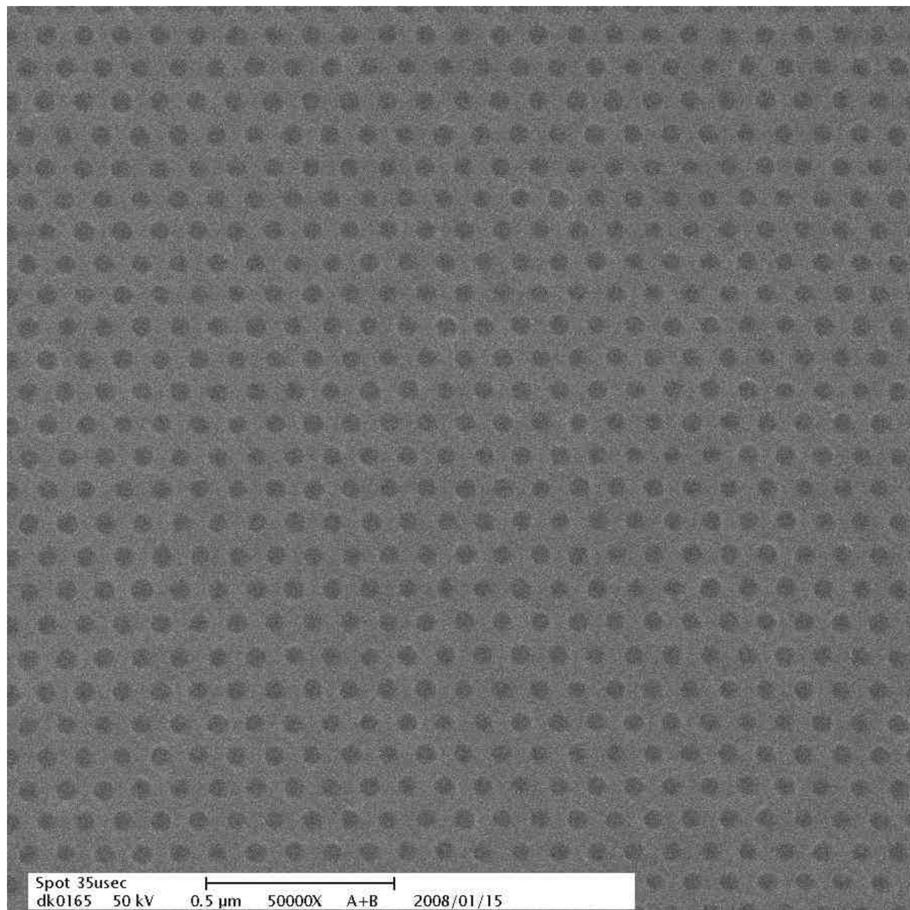
Spot Exposure

ACCEL. VOLT.	50	kV	EXT.VOLTAGE	3.9	kV
Emission CURR.	68	uA	CATHODE HEAT.	2.31	A
BEAM CURR.	100	pA	OL APERTURE	0.30	mmφ
FIELD SIZE	0.075	mm□	Dot Map	60000	dot
DOSE TIME	35.0	usec/dot	RESIST NAME	ZEP-520A	
SUBSTRATE	Si-wafer		RESIST THIKNESS	0.30	um
Development temp	room temp	℃	Development time	360	sec





100nm pitch/ 50nm hole(1)



100nm pitch/ 50nm hole(2)